ABSTRACT

Methods of Forming Trench Isolation Regions

The invention includes methods of forming trench isolation regions. In one implementation, a masking material is formed over a semiconductor substrate. The masking material comprises at least one of tungsten, titanium nitride and amorphous carbon. An opening is formed through the masking material and into the semiconductor substrate effective to form an isolation trench within semiconductive material of the semiconductor substrate. A trench isolation material is formed within the isolation trench and over the masking material outside of the trench effective to overfill the isolation trench. The trench isolation material is polished at least to an outermost surface of the at least one of tungsten, titanium nitride and amorphous carbon of the masking material. The at least one of tungsten, titanium nitride and amorphous carbon is/are etched from the substrate. Other implementations and aspects are contemplated.

FIGURE 8